**INFORMATION DISCLOSURE STATEMENT**

Applicant	:	Shveykin, Vasily I.
App. No.	:	10/689,544
Filed	:	October 20, 2003
For	:	INJECTION LASER
Examiner	:	Unknown
Group Art Unit	:	2812

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing one hundred eighteen (118) references. One hundred seventeen (117) of these cited references are of record in U.S. patent application No. 09/781,017, filed February 9, 2001, which is the parent of this Continuation application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. Copies of these 117 references are not submitted pursuant to 37 C.F.R. § 1.98(d).

Applicant directs the Examiner's attention to U.S. Patent 6,649,938 entitled "Semiconductor Optical Amplifier", issued to Bogatov et al on November 18, 2003. A copy of this patent is also enclosed. U.S. Patent 6,649,938 corresponds to U.S. Patent Application No. 09/658,642.

The references EP 0247 267 B1 and SU 1329533 A1 are cited in the international search report for the International Application No. PCT/RU99/00067 entitled "Semi-Conductor Optical Amplifier" (see International Publication No. WO 99/46838) to which U.S. Patent Application No. 09/658,642 and thus U.S. Patent 6,649,938 claims priority.

Applicant is also citing JP 60-211993. This reference was cited by the Examiner in U.S. Patent Application 09/658,642 entitled "Semiconductor Optical Amplifier" corresponding to U.S. Patent 6,649,938.

The two references EP 0849812 and SU 1455373 are cited in the international search report for the International Application No. PCT/RU99/0245 entitled "Injection Non-Coherent

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**Docket No.** DLED.004CP1C1  
**Customer No.** 20,995

Emitter" (see International Publication No. WO 00/39860), to which U.S. Patent No. 6,429,462 issued to Shveykin and entitled "Injection Incoherent Emitter," claims priority. Applicant has also cited U.S. Patent No. 6,429,462 issued to Shveykin et al.

Non-patent reference no. 39, "Optoelektronika [Optoelectronics]", Yu. R. Nosov, Radio i svyaz, [Radio and Communications], Moscow, Publ. (1989), pp. 136-143, is cited in U.S. Patent No. 6,429,462 issued to Shveykin and entitled "Injection Incoherent Emitter," at column 6, line 29-34.

Applicant is citing WIPO Publication WO 99/08352 (in Russian) which includes an abstract in English. Applicant is also citing Russian Patent RU 2,133,534. A translation of the abstract for this patent was obtained from the Delphion database ([www.delphion.com](http://www.delphion.com)) and was submitted U.S. patent application No. 09/781,017, filed February 9, 2001, which is the parent of this Continuation application, and is relied upon for an earlier filing date under 35 U.S.C. § 120.

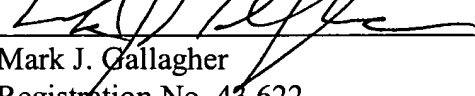
Applicant is additionally citing two Russian language articles from *Quantum Electronics* (non-patent references Nos. 104 and 105). Applicant does not have translations of the two articles; however, the articles end with brief English language abstracts.

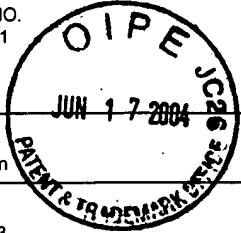
This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: 6/14/04

By:   
Mark J. Gallagher  
Registration No. 43,622  
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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. DLED.004CP1C1	APPLICATION NO. 10/689,544
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1	4,063,189	12/13/77	Scifres et al.			
	2	5,101,413	3/31/92	Botez			
	3	5,537,433	7/16/96	Watanabe			
	4	5,705,834	1/1998	Egalon et al.			
	5	5,779,924	7/1998	Krames et al.			
	6	5,793,062	8/1998	Kish, Jr. et al.			
	7	5,818,860	10/1998	Garbuzov			
	8	6,057,562	5/2000	Lee et al.			
	9	6,429,462	8/2002	Shveykin			
	10	6,649,938	11/2003	Bogatov et al.			

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	11	SU 1329533 A1	05/1998	Soviet Union			X	
	12	SU 1359833 A1	15/12/87	Soviet Union			X	
	13	1,455,373	30/01/89	Soviet Union				
	14	2,133,534	7/20/99	Russia				
	15	2,134,007	07/27/99	Russia			X	
	16	2,142,661	12/10/99	Russia			X	
	17	2,142,665	12/10/99	Russia			X	
	18	EP 0 247 267 B1	10/1991	Europe				
	19	EP 0727827 A3	21/08/96	Europe				
	20	EP 0849812 A3	24/06/98	Europe				
	21	60-211993	10/1985	Japan				
	22	WO 85/03809 A1	29/08/85	WIPO				
	23	WO 99/46838	09/1999	WIPO			X	
	24	WO 99/08352	02/1999	WIPO				

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							YES	NO
	25	WO 00/10235	02/2000	WIPO			X	
	26	WO 00/39860	07/2000	WIPO			X	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
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	28	<i>Room-Temperature CW Operation of InGaAsP Lasers on Si Fabricated by Wafer Bonding</i> , H. Wada et al., <u>IEEE Photonics Technology Letters</u> , Vol. 8, No. 2, February 1996, pp. 173-175.
	29	<i>Chemically Assisted Ion Beam Etching of GaAs, Ti, and Mo</i> , J. D. Chinn et al., <u>J. Vac. Sci. Technol. A</u> , Vol. 1, No. 2, April-June 1983, pp. 701-704.
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	32	<i>Wide Spectrum Single Quantum Well Superluminescent Diodes At 0.8 μm With Bent Optical Waveguide</i> , A. T. Semenov et al., <u>Electronics Letters</u> , Vol. 29, No. 10, May 13, 1993, pp. 854-855.
	33	<i>Superluminescent Diodes with Bent Waveguide</i> , C.-F. Lin et al., <u>IEEE Photonics Technology Letters</u> , Vol. 8, No. 2, February 1996, pp. 206-208.
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	43	<i>High Brightness Visible (660 nm) Resonant-Cavity Light-Emitting Diode</i> , K. Streubel et al., <u>IEEE Photonics Technology Letters</u> , Vol. 10, No. 12, December 1998, pp. 1685-1687.
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EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	

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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	45	<i>High-power, high-efficiency 1.3 <math>\mu</math>m superluminescent diodes with a buried bent absorbing guide structure</i> , Haruo Nagai et al., <i>Applied Physics Letters</i> , Volume 54, Number 18, May 1989, pp. 1719-1721.
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	50	<i>High-Power Near-Diffraction-Limited Tapered Amplifiers at 1064 nm for Optical Intersatellite Communications</i> , P. Chazan et al., <i>IEEE Photonics Technology Letters</i> , Vol. 10, No. 11, November 1998, pp. 1542-1544.
	51	<i>Extremely Low Power Consumption Semiconductor Optical Amplifier Gate for WDM Applications</i> , T. Ito et al., <i>Electronics Letters</i> , Vol. 33, No. 21, October 9, 1997, pp. 1791-1792.
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	61	<i>Semiconductor Optical Amplifiers</i> , N. Anders Olsson, <i>Proceedings of IEEE</i> , Vol. 80, No. 3, March 1992, pp. 375-382.
	62	<i>Ultra-Low-Reflectivity Semiconductor Optical Amplifiers Without Antireflection Coatings</i> , W. Rideout et al., <i>Electronics Letters</i> , Vol. 26, No. 1, January 4, 1990, pp. 36-38.
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	68	<i>Semiconductor Laser Optical Amplifiers for Use in Future Fiber Systems</i> , M. J. O'Mahony, <u>Journal of Lightwave Technology</u> , Vol. 6, No. 4, April 1988, pp. 531-544.
	69	<i>New Inline Wideband Dynamic Semiconductor Laser Amplifier Model</i> , A. J. Lowery, <u>IEEE Proceedings</u> , Vol. 135, Pt. J, No. 3, June 1988, pp. 242-250.
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	91	<i>High-Power, Near-Diffraction-Limited Large-Area Traveling-Wave Semiconductor Amplifier</i> , L. Goldberg et al., <u>IEEE Journal of Quantum Electronics</u> , Vol. 29, No. 6, June 1993, pp. 2028-2043.
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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
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